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Shot noise of a quantum dot with non-Fermi liquid correlations

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The shot noise of a one-dimensional wire interrupted by two barriers shows interesting features related to the interplay between Coulomb blockade effects, Luttinger correlations and discrete excitations. At small bias the Fano factor reaches the lowest attainable value, 1/2, irrespective of the ratio of the two junction resistances. At larger voltages this asymmetry is power-law renormalized by the interaction strength. We discuss how the measurement of current and these features of the noise allow to extract the Luttinger liquid parameter.

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A comprehensive understanding of the transport properties of mesoscopic conductors can be achieved with the study of both the average current and its fluctuations. Unlike equilibrium noise, linked to the conductance by the fluctuation-dissipation theorem, shot noise provides further understanding not related to the average current. Noise is typically very sensitive to correlation mechanisms arising either due to statistics, interference phenomena and interactions [1, 2]. One of the most striking effects recently observed is the measurement [3, 4] of the fractional charge in the Fractional Quantum Hall Effect.

The understanding of the role of electron interaction on shot noise is far from being complete. At the present most of the attention is devoted to two classes of systems, mesoscopic junctions in the Coulomb blockade regime and one dimensional (1D) wires where electron interaction lead to a Luttinger liquid behaviour. In single electron tunnelling transistors noise has been studied both in the sequential tunnelling [5, 6, 7, 8] and in the cotunnelling [9, 10] regime. Deviation of the shot noise from the Poisson value was predicted when two charge states are almost degenerate. As a function of the transport voltage, the Fano factor shows dips in correspondence of the steps of the Coulomb staircase. Experiments on the shot noise suppression due to Coulomb blockade effects has been performed by Birk *et al.* [11] with a good agreement with the theoretical prediction. As a function of the gate voltage, shot noise exhibits a periodic suppression below the Poisson value [7].

Another situation where interactions have a drastic consequence [12] is in 1D systems. Here, there are no fermionic quasiparticle, and the low energy excitations consist of independent long-wavelength oscillations of the charge and spin density, which propagate with different velocities. The density of states has a power-law behaviour and the transport properties cannot be described in terms of the conventional Fermi-liquid approach. A Luttinger liquid (LL) with an arbitrarily small barrier leads to a complete suppression of transport at low energies [13]. By now there are several works which show the emergence of a LL behaviour. These studies embrace a variety of physical systems as quantum wires [14], carbon nanotubes [15] and edge state in the Fractional Quantum Hall effect [16]. Shot noise in systems with LL correlations provides important informations and a number of very interesting properties have been found so far. In addition to the possibility to measure the fractional charge, interactions renormalize the singularity at the "Josephson" frequency [17]. Other clear signatures include the complete locking of the shot noise in coupled LL [18]. We thus expect that a single electron transistor made of a 1D system will have a rather rich phenomenology.

In this Letter we study the shot noise of a quantum dot, formed by two barriers, in a 1D wire with LL correlations in the sequential tunnelling regime. We consider the quantum dot with discrete energy excitations, ranging from the "single resonant level" to a continuum distributions. Beside the suppression of the shot noise due to the Coulomb blockade [6], we find additional effects induced by the non-Fermi liquid correlations. These last features are what we are mainly looking at. We show that the shot noise reveals several unambiguous evidences of Luttinger correlations and presents new and complementary informations with respect to the current measurements. The results can be used to test independently the non-Fermi liquid nature of the system.

The Hamiltonian of the system is composed by the term which describes electrons in the quantum wire and the scattering induced by the presence of the two barriers. In the bosonized form the part due to an homogeneous spinless interacting one-dimensional electron gas is expressed in terms of an harmonic field operators ($\hbar = 1$) $[\Pi(x), \Theta(x')] = i\delta(x - x')$[12]

$$H_0 = \frac{v_{\rm F}}{2} \int {\rm d}x \left\{ \Pi^2(x) + \frac{1}{g^2} [\partial_x \Theta(x)]^2 \right\} . \qquad (1)$$

The interaction parameter is $g^{-2} = 1 + V(q = 0)/\pi v_{\rm F}$ with $v_{\rm F}$ the Fermi velocity and $V(q)$ the Fourier transform of the electron-electron interaction. The excitations of Eq.(1), at fixed average density $\rho_0 = k_{\rm F}/\pi$, are collective density waves with dispersion $\omega(q) = v_{\mathrm{F}}|q|/g$. The scattering is due to the left (l) and to the right (r) barriers at positions $x = \pm d/2$ with different heights $U_{\mathrm{l,r}}$. The corresponding tunnelling Hamiltonian is [13]

$$H_{\mathrm{T}} = \sum_{p=\pm}(U_{\mathrm{l}} + pU_{\mathrm{r}}) \prod_{s=\pm} \cos\pi(N^s + n_0\delta_{s,-} - \frac{1-p}{4}) \quad (2)$$

where $N^{\pm} = [\Theta(d/2) \pm \Theta(-d/2)]/\sqrt{\pi}$, with N^- the deviation of the number of electrons in the dot from the mean value, $n_0 = d\rho_0$, and $N^+/2$ the imbalanced electrons between the left and right leads. The coupling to the source-drain bias V and the gate voltage V_{g} is given by $H_{\mathrm{V}} = -e(VN^+/2 + \alpha V_{\mathrm{g}} N^-)$, with α the ratio between gate and total capacitances.

The zero-frequency power spectrum of the noise is given by the current-current correlation function

$$S = \int_{-\infty}^{\infty} dt \, [\langle \delta I(t)\delta I(0)\rangle + \langle \delta I(0)\delta I(t)\rangle] \,, \quad (3)$$

where $\delta I(t) \equiv I(t) - \langle I\rangle$ is the (total) current fluctuation operator with respect to the average $\langle I\rangle$. Since we are interested in the zero-frequency noise, due to continuity equation and simmetries of the correlation functions, it is sufficient to study fluctuations in the current through the right or the left junctions $I_{\mathrm{r/l}}(t) = e\dot{\Theta}(\pm\frac{d}{2}, t)/\sqrt{\pi}$.

The current fluctuations are determine by the dynamics of the variables $N^{\pm}$ under the influence of the electrostatic fields in the tunnelling potential (2). We consider the sequential tunnelling regime, neglecting contributions from coherent processes. This assumption is valid in the weak tunneling regime for not too low temperatures [20]. This is exactly the regime relevant for available experiments. For high barriers the dynamics is dominated by tunnelling through the left and right junctions with resistances R_{l} and R_{r} respectively. There are two characteristic energy scales. The energy E_{c} has to be supplied in order to transfer one extra charge to the island from the neutral configuration. It determines the dot ground state chemical potential with n electrons $\mu(n) = 2E_{\mathrm{c}}(n - n_{\mathrm{g}})$, with $n_{\mathrm{g}} = n_0 + \alpha e V_{\mathrm{g}}/2E_{\mathrm{c}} - 1/2$. A discrete energy ε is necessary to further excite the discrete plasmon modes inside the dot. An explicit expression of these two energy scales depends on the microscopic and circuital details of the system [20]. The coupling to gates and the presence of possible long range electron interactions tend to modify these values [21]. For these reasons we will treat them as independent parameters.

The shot noise is obtained from the solution of a time dependent master equation for the occupation probabilities of charges in the dot as described in Ref. 6. The new ingredients here are the tunnelling rates that depend on the Luttinger correlations [20]. For a tunnelling process, to which is associated a change E in the electrostatic energy, the rate is proportional to $\gamma(E) = \sum_{p=0}^{\infty} \Gamma(p + 1/g) f(E - p\varepsilon, g)/p!$, with $f(E, g) = \mathrm{e}^{E/2T} |\Gamma\left(1/(2g) + iE/2\pi T\right)|^2$ ($k_{\mathrm{B}} = 1$). Note that this expression is obtained by assuming a thermal distribution for the plasmons in the leads and in the dot with $T \ll \varepsilon$. This implies that the initial dot state is always the ground state. The plasmon excitations are present only in the final states. Such a description is appropriated when the relaxation processes are faster than the tunnelling processes. In this case any excited state will decay into the ground state long before the next electron tunnels in the dot. The possibility to tune the external bias voltage in the energy E allow to investigate the discreteness of the plasmon energy, ranging from the "single resonant level" ($E < \varepsilon$) where no plasmon are excited, to the continuum of plasmon distribution ($E \gg \varepsilon$). In these two extreme cases the rates acquire the simplifed form $\gamma(E) \approx f(E, g)$ and $\gamma(E) \approx f(E, g/2)$ respectively. In the first case the power law correlations are only due to the Luttinger liquid nature of the leads. In the latter the dot itself acts as a Luttinger reservoir.

In the following we will present the case of asymmetric barriers characterized by ratio $R = R_{\mathrm{r}}/R_{\mathrm{l}}$. As we are interested in the shot noise we consider only low temperatures $T \ll eV$. We will consider results for the Fano factor $F \equiv S/2e|\langle I\rangle|$. A detailed discussion of the behavior of the average current as a function of the external voltages as been given in [20]. The Fano factor is presented in Fig. 1 with $R = 10$ and $T = 0$ for two different ratio $\varepsilon/E_{\mathrm{c}} = 0.1$ (a) and $\varepsilon/E_{\mathrm{c}} = 1.6$ (b). These two values are chosen in order to show the different effects of the discrete plasmon modes. The noise is periodic in the n_{g}-variable. For clarity in the figure we present the results for $-1/2 < n_{\mathrm{g}} < 3/2$ where two Coulomb peaks of the linear conductance, centered at $n_{\mathrm{g}} = 0, 1$, are present . Different features of electron-electron interactions will be now described depending on the small, large and intermediate voltage regions. The numerical results can be corroborated by analytical calculations in several limits.

Let us start with the small voltage limit. Near to the resonance $n_{\mathrm{g}} \approx 0$, for $eV < 4E_{\mathrm{c}}$ two charge values contribute predominantly to the transport. The Coulomb blockade region are here delimitated by the diamond lines $E_{\pm} \equiv eV/2 \pm 2E_{\mathrm{c}} n_{\mathrm{g}} = 0$. In this regime the Fano factor assumes the form

$$F = 1 - \frac{2R\gamma_+\gamma_-}{[(1 + e^{-E_-/T})\gamma_- + R(1 + e^{-E_+/T})\gamma_+]^2} \quad (4)$$

with $\gamma_{\pm} \equiv \gamma(E_{\pm})$. By inspection of (4) one can see that the temperature plays a significant role *only* near the edges of the diamond lines $|E_+| \leq T$ or $|E_-| \leq T$ (see later). Out from this region the Fano factor is well approximated by the $T = 0$ value. We first discuss the case of low bias voltages $E_{\pm} < \varepsilon$ where it is not possible to excite plasmons. At $T = 0$ the Fano is $F = (E_-^{2\nu(g)} + R^2 E_+^{2\nu(g)})/(E_-^{\nu(g)} + RE_+^{\nu(g)})^2$, with $\nu(g) = -1 + 1/g$. For non-interacting leads ($g = 1$) F is voltage independent $F=(1+R^2)/(1+R)^2$ and assumes the lowest value ($F=1/2$) *only* for symmetric barriers.

In the interacting case $g<1$ the Fano is *always* suppressed to the 1/2 value, at a given voltage ratio $4E_\mathrm{c}n_\mathrm{g}/eV=(1-R^{1/\nu(g)})/(R^{1/\nu(g)}+1)$. On increasing the interaction strength ($g\to 0$) the resonant point moves towards $n_\mathrm{g}=0$; away from it F tends to the Poisson value (see Fig. 1(b) at $eV<4E_\mathrm{c}$, and Fig. 2). This behaviour is also confirmed by the temperature scaling near to the edges of the Coulomb blockade region. In the limits $|E_\pm|\ll T$ one has

$$F\approx 1-c_\pm(T/eV)^{\nu(g)}\,,$$

with $c_\pm\sim R^{\pm 1}$. For non-interacting leads, F is temperature independent, increasing the interactions the Fano factor approaches as a power law the values $F=1$. If $\varepsilon\ll E_\mathrm{c}$ (Fig. 1(a)) one can also reach the regime $\varepsilon\ll E_\pm$, still using only two charge states, $eV<2E_\mathrm{c}$. In this case the Fano factor results from the contribution by the continuum of excited plasmons. Its expression as a function of resistance and voltages is still valid but with the replacement $\nu(g)\to\nu(g/2)$.

The strong interplay between Coulomb blockade features and non-Fermi liquid correlations is also very clearly revealed at larger voltages $eV\gtrsim 4E_\mathrm{c}$, if the asymmetry of the barriers is not too small. As a function of the voltage bias and in the limit $eV\gg\varepsilon$, (cf. Fig. 3) the Fano factor shows a series of dips and it saturates to a constant value, F_∞, for $eV\gg E_\mathrm{c}$. In the orthodox theory of Coulomb blockade in small metal junctions, the decrease of the Fano factor is driven by E_c and it is attributed to the correlations present at the degeneracy points. A detailed analysis of the numerical results allows to extract the following behaviour, valid for enough strong asymmetry $R\gg 1$, for the distance in the bias voltage between two successive dips at fixed voltage gate δV_dip

$$\frac{e\delta V_\mathrm{dip}}{4E_\mathrm{c}}=\frac{R^{1/\nu(g/2)}+1}{R^{1/\nu(g/2)}-1}\,, \tag{5}$$

This fitting behaviour is obtained by extrapolating, at larger voltages, the dip position lines $eV(n)(1-R^{1/\nu(g/2)})=4E_\mathrm{c}(n_\mathrm{g}-n)(R^{1/\nu(g/2)}+1)$ founded previously, in the continuum case for the n and $n+1$ charges, and considering the corresponding distance $\delta V_\mathrm{dip}\equiv V(n+1)-V(n)$.

In the asymptotic regime we find substancial modifications also to the Fano-Schottky theorem $F_\infty=(1+R^2)/(1+R)^2$ [6]. We extract the power law behaviour

$$F_\infty=\frac{1+R^{2/\nu(g/2)}}{[1+R^{1/\nu(g/2)}]^2}\,. \tag{6}$$

We can see that Luttinger correlations lead, instead of R, a new effective resistance ratio $R^{1/\nu(g/2)}$ that scales with a power law in g, in agreement with the results at small voltages. The properties of the Fano factor given so far, allow to extract the properties of the transistor and the value of the Luttinger liquid parameter without resorting to any fitting procedure.

Let us switch now to the more intricate region $eV\gtrsim 2E_\mathrm{c},\varepsilon$, where Coulomb features, discrete nature of the excited plasmon states, and Luttinger correlations are present simultaneously (cf. Fig. 1(b)). Apart from the asymptotic regime $eV\gg E_\mathrm{c},\varepsilon$, where $F\to F_\infty$ as in (6), the physics is quite different depending on the intensity of the interaction. For strong interactions, $g<1/2$, F is similar to the one described above in the continuum limit. Qualitative differences are instead revealed in the weak interaction limit $1/2<g<1$. Here, the threshold of the Coulomb dips is *not* renormalized by the interaction. Moreover superimposed to these dips there is an additional structure with a width proportional to $|\varepsilon-2E_\mathrm{c}|$. These new features are due to the transport via excited states. Note that the effect of correlations in these channels can also lead to a change of the curvature in the Fano factor, differently from the processes associated with the ground state to ground state transitions. This is visible by looking at the different colors of the diamont-like structures (e.g. red and green features in Fig. 1(b) for $g=1$). These two colors represent the two different way of entering/leaving in/from a plasmon excited state of the dot. Indeed, by considering the $n\to n+1\to n$ transition, we can have either one electron that enters in the dot, creating an excited plasmon state of the $n+1$ charge or one elctron that leaves the dot from the $n+1$ ground state in an excited plasmon state of n charges. These two processes can be discriminated in the Fano behaviour giving informations on the different excited states that contribute to transport.

In conclusion we demonstrated how the presence of Luttinger correlations changes drastically the behaviour of the Fano factor with respect to the orthodox theory. In particular we showed that the interaction strongly renormalizes the position of the dips, filtering at small voltages the degrees of correlations. A crucial role is played by the barrier asymmetry that is shown to be power law renormalized by the interaction strength. Very recently Nazarov and Glazman [22] obtained the renormalization group equation for the transmission in one-dimensional wire interrupted by a double-barrier structure with a resonant level. It would be important to extend the results on noise beyond the sequential tunnelling approximation by emplying the approach of Ref. [22]. We expect that the predictions made in this work are amenable of experimental verification. Indeed realizations of the one-dimensional quantum dot system we considered has been recently achieved in a cleaved-edge overgrowth quantum wire with two impurities [14] and in carbon nanotubes with buckles [19]. Experimental results are already available on the linear and non-linear transport current. New experiments on the shot noise would be of interest in order to test the new predictions presented in this work.

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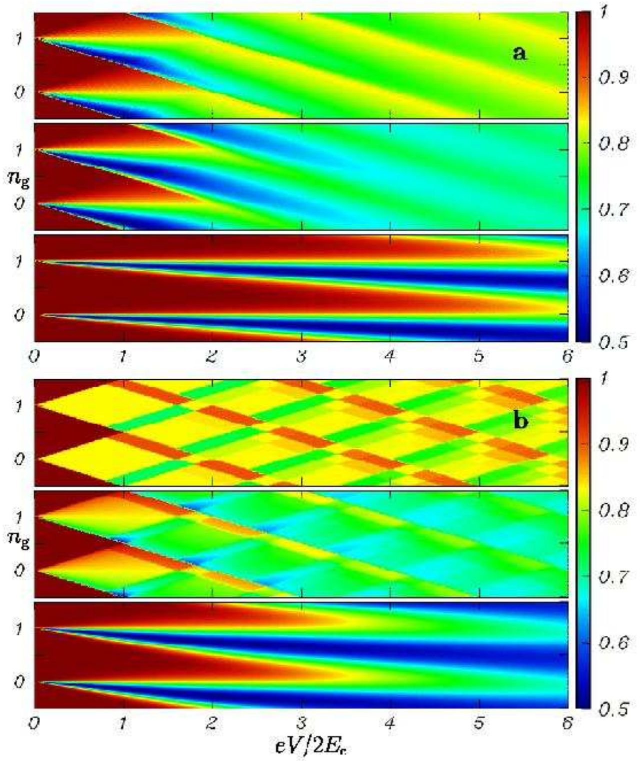

FIG. 1: Density plots of the Fano factor $F = S/2e|\langle I\rangle|$ in the $eV/2E_{\rm c}$, $n_{\rm g}$-plane for $R = 10$, $T = 0$ and interaction strength $g = 1, 0.8, 0.2$. The discretization energy are: (a) $\varepsilon/E_{\rm c} = 0.1$; (b) $\varepsilon/E_{\rm c} = 1.6$. Color code (right).

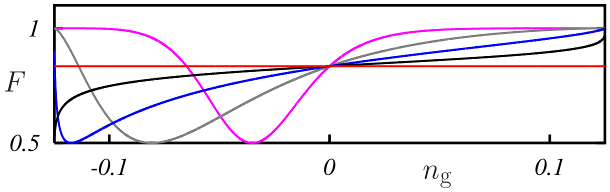

FIG. 2: Fano factor as a function of the gate voltage $n_{\rm g}$, for $T = 0$, $R = 10$, $eV/2E_{\rm c} = 0.25$, $\varepsilon/E_{\rm c} = 1.6$, with interaction strength $g = 1$ red, $g = 0.8$ black, $g = 0.6$ blue, $g = 0.4$ grey, $g = 0.2$ magenta.

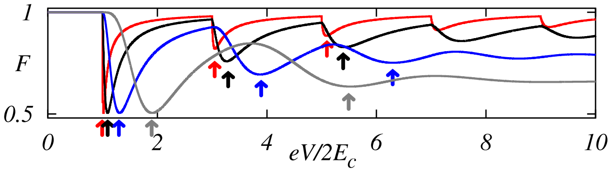

FIG. 3: Fano factor as a function of the transport voltage $eV/2E_{\rm c}$, for $T = 0$, $R = 100$, $n_{\rm g} = 0.5$, $\varepsilon/E_{\rm c} = 0.01$, with $g = 1$ red, $g = 0.8$ black, $g = 0.6$ blue, $g = 0.4$ grey. The arrows indicate the Fano dips whose distance at a given interaction (see different colors) follow equation (5).